

Titles of most frequently occurring classifications of patents returned
from a search of 10/563,269 on Jan 30 , 2008

- 20 257/E33.028 (0 OR, 20 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/E33.001 .LIGHT EMITTING SEMICONDUCTOR DEVICES HAVING A POTENTIAL OR A SURFACE BARRIER, PROCESSES OR APPARATUS PECULIAR TO THE MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF
 - 257/E33.002 ..Device characterized by semiconductor body (EPO)
 - 257/E33.013 ...Material of active region (EPO)
 - 257/E33.023Comprising only Group III-V compound (EPO)
 - 257/E33.026Ternary or quaternary compound (e.g., AlGaAs) (EPO)
 - 257/E33.028Including nitride (e.g., AlGaN) (EPO)
- 19 257/103 (6 OR, 13 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/79 .INCOHERENT LIGHT EMITTER STRUCTURE
 - 257/103 ..With particular semiconductor material
- 11 257/96 (4 OR, 7 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/79 .INCOHERENT LIGHT EMITTER STRUCTURE
 - 257/94 ..With heterojunction
 - 257/96 ...Plural heterojunctions in same device
- 9 438/46 (5 OR, 4 XR)
 - Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
 - 438/22 .MAKING DEVICE OR CIRCUIT EMISSIVE OF NONELECTRICAL SIGNAL
 - 438/46 ..Compound semiconductor
- 9 257/94 (0 OR, 9 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/79 .INCOHERENT LIGHT EMITTER STRUCTURE
 - 257/94 ..With heterojunction
- 8 372/45.01 (3 OR, 5 XR)
 - Class 372 COHERENT LIGHT GENERATORS
 - 372/39 .PARTICULAR ACTIVE MEDIA
 - 372/43.01 ..Semiconductor
 - 372/44.01 ...Injection
 - 372/45.01Particular confinement layer
- 8 257/76 (1 OR, 7 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/76 .SPECIFIED WIDE BAND GAP (1.5eV) SEMICONDUCTOR MATERIAL OTHER THAN GaAsP or GaAlAs
- 7 372/46.01 (4 OR, 3 XR)
 - Class 372 COHERENT LIGHT GENERATORS
 - 372/39 .PARTICULAR ACTIVE MEDIA
 - 372/43.01 ..Semiconductor
 - 372/44.01 ...Injection
 - 372/46.01Particular current control structure
- 7 257/190 (2 OR, 5 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 257/183 .HETEROJUNCTION DEVICE
 257/190 ..With lattice constant mismatch (e.g., with buffer layer to accommodate mismatch)

6 257/E33.03 (0 OR, 6 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 257/E33.001 .LIGHT EMITTING SEMICONDUCTOR DEVICES HAVING A POTENTIAL OR A SURFACE
 BARRIER, PROCESSES OR APPARATUS PECULIAR TO THE MANUFACTURE OR TREATMENT OF SUCH
 DEVICES, OR OF PARTS THEREOF
 257/E33.002 ..Device characterized by semiconductor body (EPO)
 257/E33.013 ...Material of active region (EPO)
 257/E33.023Comprising only Group III-V compound (EPO)
 257/E33.029Characterized by doping material (EPO)
 257/E33.03Nitride compound (EPO)

6 257/97 (0 OR, 6 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 257/79 .INCOHERENT LIGHT EMITTER STRUCTURE
 257/94 ..With heterojunction
 257/96 ...Plural heterojunctions in same device
 257/97More than two heterojunctions in same device